SUB E1

8. (New) The semiconductor light-emitting device of claim 1, wherein a thickness of said well layer is approximately 30 Å and a thickness of said barrier layer is approximately 70 Å.

9. (New) The semiconductor light-emitting device of claim 1, further comprising:

a cap layer formed on said light-emitting layer; and

a p-type clad layer formed on said cap layer.

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10. (New) The semiconductor light-emitting device of claim 9, wherein a thickness of said p-type clad layer is in a range of approximately 180 Å to 500 Å, and a light emitted comprises green light in a wavelength range of approximately 510 nm to 530 nm.

11. (New) The semiconductor light-emitting device of claim 10, wherein said thickness of said p-type clad layer is in a range of approximately 240 Å to 360 Å.

12. (New) The semiconductor light-emitting device of claim 9, wherein a thickness of said p-type clad layer is in a range of approximately 90 Å to 390 Å, and a light emitted comprises blue light in a wavelength range of approximately 460 nm to 475 nm.

13. (New) The semiconductor light-emitting device of claim 12, wherein said thickness of said p-type clad layer is in a range of approximately 120 Å to 300 Å.

14. (New) The semiconductor light-emitting device of claim 9, wherein said p-type clad layer comprises p-type doped $Al_xGa_{1-x}N$, where x ranges from approximately 0.10 to 0.14.

15. (New) A group III nitride compound semiconductor light-emitting device, comprising:

a light-emitting layer of a multilayer quantum well structure composed of alternately laminated well layers and barrier layers; and

an n-type clad layer being in contact with said light-emitting layer,

wherein said n-type clad layer is made thicker than each of said barrier layers, said n-type clad layer is formed of a material substantially the same as said barrier layers, said